EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	286	(semiconductor and second and region and first and third and first and third and flourth and electrode and sixth and eighth and (layer or film) and (insulat\$3 or dielectric) and gate).	US-PGPUB; USPAT; USOCR	OR	ON	2009/05/29 17:14
L2	9	(semiconductor and second and region and first and third and fourth and fifth and electrode and sixth and eighth and (layer or film) and (insulat\$3 or dielectric) and gate and conductive and type and concentration and impurity and high).	US-PGPUB; USPAT; USOCR	OR .	ON	2009/05/29 17:15

5/29/2009 5:28:44 PM

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